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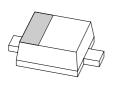
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Kind regards,

Team Nexperia



200 mA low V_F MEGA Schottky barrier rectifier Rev. 01 — 15 May 2009 P

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD323F (SC-90) small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 0.2 A
- Reverse voltage: $V_R \le 40 V$
- Low forward voltage
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Ultra high-speed switching
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \circ C$ unless otherwise specified.

)	I					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)} average forward current		square wave; $\delta = 0.5;$ f = 20 kHz				
		$T_{amb} \le 130 \ ^{\circ}C$	<u>[1]</u> -	-	0.2	А
		$T_{sp} \le 145 \ ^{\circ}C$	-	-	0.2	А
V _R	reverse voltage		-	-	40	V
V _F	forward voltage	I _F = 0.2 A	-	520	600	mV
I _R	reverse current	$V_R = 40 V$	-	0.7	10	μΑ
-						

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



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2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	e Graphic symbol
1	cathode	[1]	
2	anode		1 1 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Order	ing informati	on	
Type number	Package		
	Name	Description	Version
PMEG4002EJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG4002EJ	1N

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C	-	40	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5;$ f = 20 kHz			
		$T_{amb} \le 130 \ ^{\circ}C$	<u>[1]</u> _	0.2	А
		$T_{sp} \le 145 \ ^{\circ}C$	-	0.2	А
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms};$ $\delta \le 0.25$	-	2.6	A
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	[2] -	2.75	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4]	385	mW
			[3][5]	695	mW
			[3][1]	1045	mW

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Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] $T_j = 25 \ ^{\circ}C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	325	K/W
			[4] _	-	180	K/W
			[5] _	-	120	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	25	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[5] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.

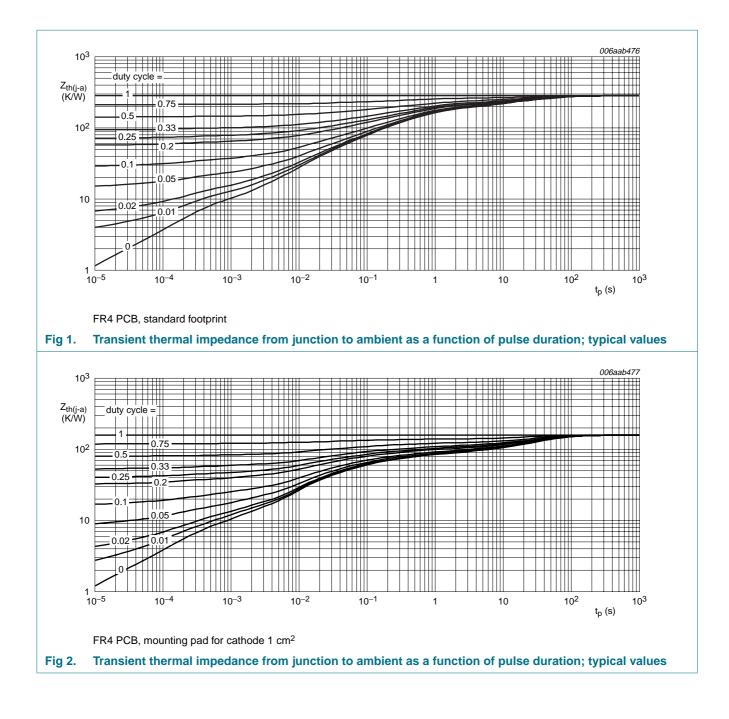
[6] Soldering point of cathode tab.

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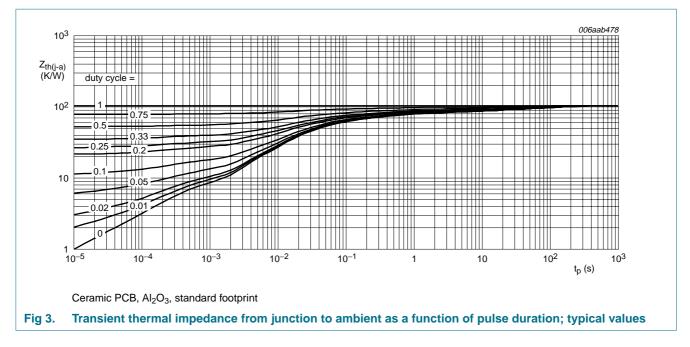
200 mA low V_F MEGA Schottky barrier rectifier



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200 mA low V_F MEGA Schottky barrier rectifier



7. Characteristics

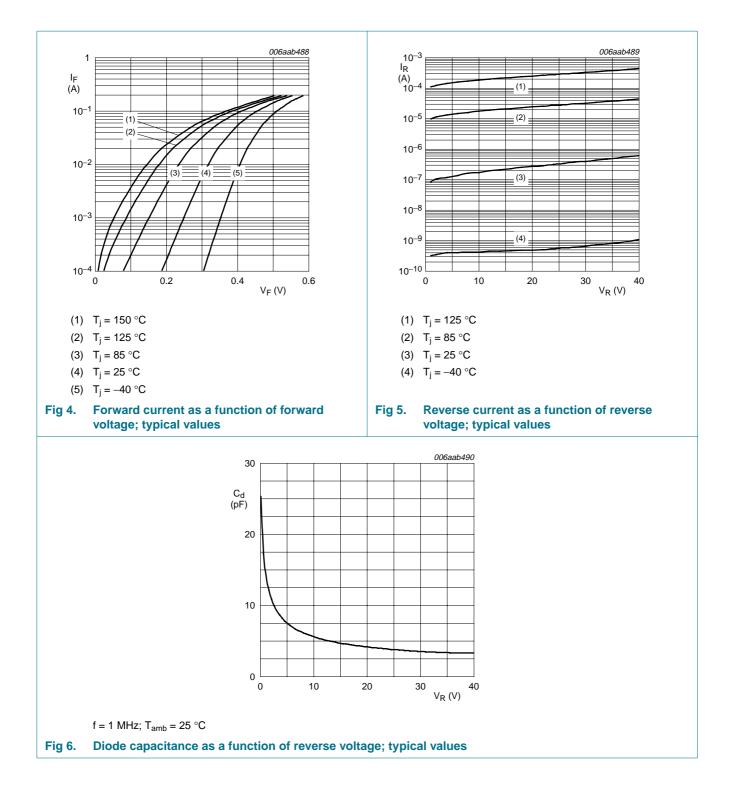
Table 7.Characteristics

$T_i = 25 \circ C$ unless	otherwise	specified.
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I _F = 0.1 mA	-	190	220	mV
		$I_F = 1 \text{ mA}$	-	250	290	mV
	I _F = 10 mA	-	320	360	mV	
	I _F = 100 mA	-	440	500	mV	
	I _F = 200 mA	-	520	600	mV	
I _R	I _R reverse current	V _R = 10 V	-	0.2	0.3	μA
		V _R = 25 V	-	0.3	0.5	μA
		V _R = 40 V	-	0.7	10	μA
C _d	diode capacitance	f = 1 MHz				
		V _R = 1 V	-	14	-	pF
		V _R = 10 V	-	6	-	pF
t _{rr}	reverse recovery time	9	<u>[1]</u> -	5	-	ns

[1] When switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100 \Omega$; measured at $I_R = 1$ mA.

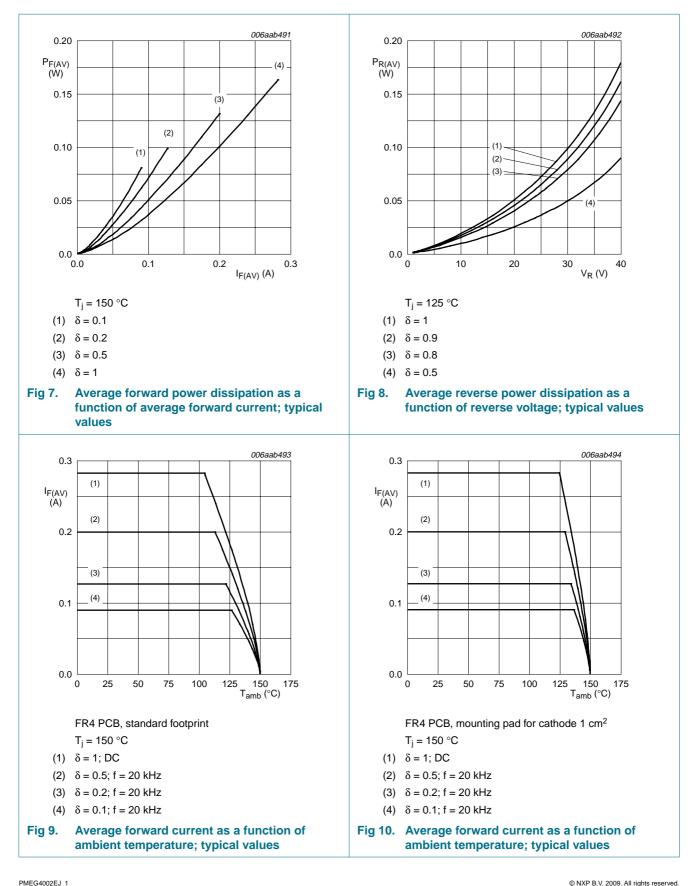
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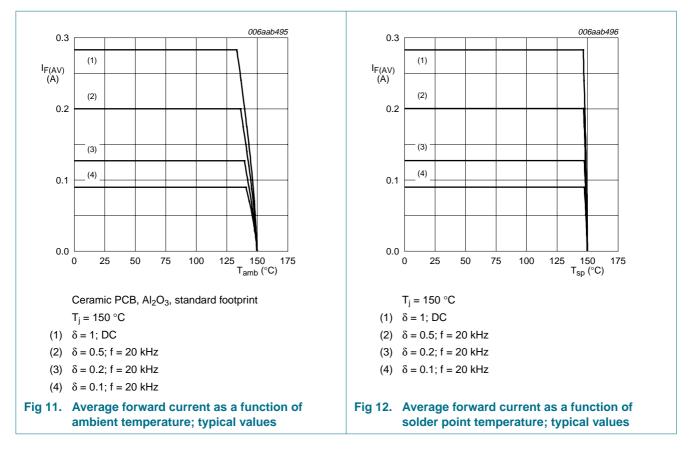
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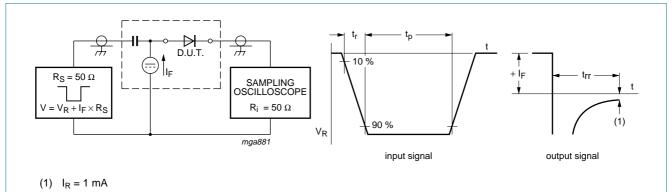
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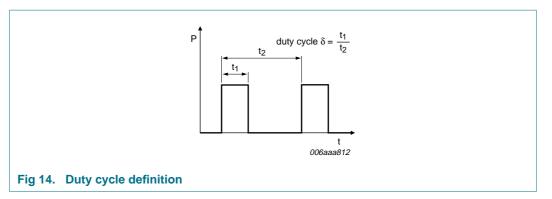
8. Test information



Input signal: reverse pulse rise time $t_r = 0.6$ ns; reverse voltage pulse duration $t_p = 100$ ns; duty cycle $\delta = 0.05$ Oscilloscope: rise time $t_r = 0.35$ ns

Fig 13. Reverse recovery time test circuit and waveforms

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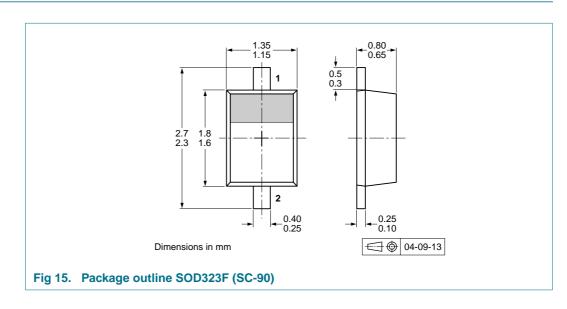
The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

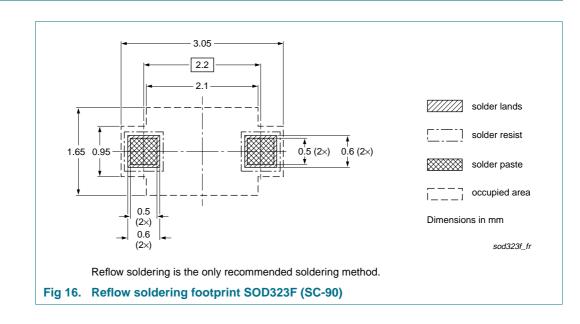


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10. Packing information

Type number Package Description Packing quant		
3000	10000	
-115	-135	
	-115	

11. Soldering



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12. Revision history

Table 9. Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4002EJ_1	20090515	Product data sheet	-	-

200 mA low V_F MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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PMEG4002EJ_1
Product data sheet

200 mA low V_F MEGA Schottky barrier rectifier

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